

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74AC125P, TC74AC125F, TC74AC125FN, TC74AC125FT
TC74AC126P, TC74AC126F, TC74AC126FN
TC74AC125P/F/FN/FT QUAD BUS BUFFER
TC74AC126P/F/FN QUAD BUS BUFFER

(Note) The JEDEC SOP (FN) is not available in Japan.

The TC74AC125/126 are advanced high speed CMOS QUAD BUS BUFFERs fabricated with silicon gate and double-layer metal wiring C²MOS technology.

They achieve the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

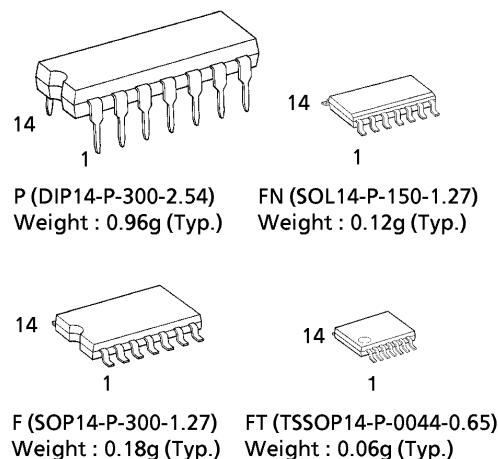
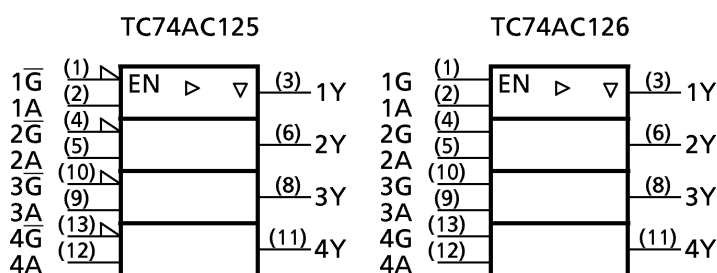
The TC74AC125 requires the 3-state control input $\overline{G}$ to be set high to place the output into the high impedance state, whereas the TC74AC126 requires the control input to be set low to place the output into high impedance.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

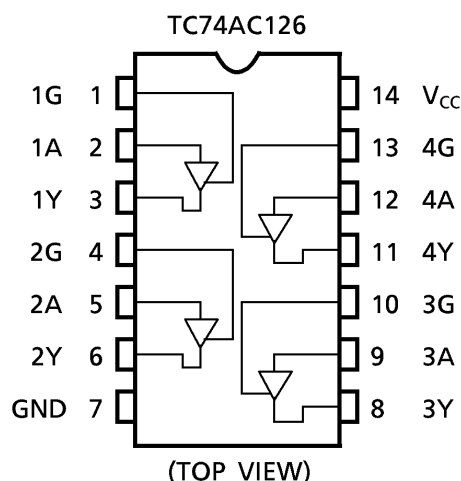
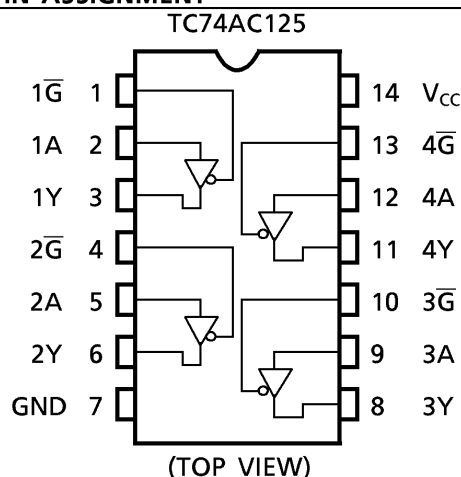
FEATURES:

- High Speed..... $t_{pd} = 4.0\text{ns}(\text{typ.})$ at $V_{CC} = 5\text{V}$
- Low Power Dissipation..... $I_{CC} = 8\mu\text{A}(\text{Max.})$ at $T_a = 25^\circ\text{C}$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC}(\text{Min.})$
- Symmetrical Output Impedance..... $|I_{OH}| = |I_{OL}| = 24\text{mA}(\text{Min.})$
 Capability of driving 50Ω transmission lines.
- Balanced Propagation Delays..... $t_{PLH} \approx t_{PHL}$
- Wide Operating Voltage Range..... $V_{CC}(\text{opr}) = 2\text{V} \sim 5.5\text{V}$
- Pin and Function Compatible with 74F125/126

IEC LOGIC SYMBOL



PIN ASSIGNMENT



TRUTH TABLE

TC74AC125

INPUTS		OUTPUTS
$\overline{G}$	A	Y
H	X	Z
L	L	L
L	H	H

X: Don't Care
Z: High Impedance

TC74AC126

INPUTS		OUTPUTS
G	A	Y
L	X	Z
H	L	L
H	H	H

X: Don't Care
Z: High Impedance

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	$-0.5 \sim 7.0$	V
DC Input Voltage	V_{IN}	$-0.5 \sim V_{CC} + 0.5$	V
DC Output Voltage	V_{OUT}	$-0.5 \sim V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 50	mA
DC Output Current	I_{OUT}	± 50	mA
DC V_{CC} /Ground Current	I_{CC}	± 100	mA
Power Dissipation	P_D	500 (DIP)* / 180 (SOP/TSSOP)	mW
Storage Temperature	T_{stg}	$-65 \sim 150$	°C

*500mW in the range of $T_a = -40^\circ\text{C} \sim 65^\circ\text{C}$. From $T_a = 65^\circ\text{C}$ to 85°C a derating factor of $-10\text{mW}/^\circ\text{C}$ should be applied up to 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	$2.0 \sim 5.5$	V
Input Voltage	V_{IN}	$0 \sim V_{CC}$	V
Output Voltage	V_{OUT}	$0 \sim V_{CC}$	V
Operating Temperature	T_{opr}	$-40 \sim 85$	°C
Input Rise and Fall Time	dt/dV	$0 \sim 100$ ($V_{CC} = 3.3 \pm 0.3\text{V}$) $0 \sim 20$ ($V_{CC} = 5 \pm 0.5\text{V}$)	ns / V

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	Ta = 25°C			Ta = -40~85°C		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Input Voltage	V _{IH}		2.0 3.0 5.5	1.50 2.10 3.85	— — —	— — —	1.50 2.10 3.85	— — —	V
Low - Level Input Voltage	V _{IL}		2.0 3.0 5.5	— — —	— — —	0.50 0.90 1.65	— — —	0.50 0.90 1.65	V
High - Level Output Voltage	V _{OH}	V _{IH} or V _{IL}	I _{OH} = -50μA 2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5	— — —	1.9 2.9 4.4	— — —	V
				I _{OH} = -4mA 3.0 4.5	2.58 3.94	— —	2.48 3.80	— —	
				I _{OH} = -24mA I _{OH} = -75mA*	— —	— —	3.85 —	— —	
Low - Level Output Voltage	V _{OL}	V _{IH} or V _{IL}	I _{OL} = 50μA 2.0 3.0 4.5	— — —	0.0 0.0 0.0	0.1 0.1 0.1	— — —	0.1 0.1 0.1	V
				I _{OL} = 12mA 3.0 4.5	— —	0.36 0.36	— —	0.44 0.44	
				I _{OL} = 24mA I _{OL} = 75mA*	— —	— —	— —	1.65 1.65	
3 - State Output Off - State Current	I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = V _{CC} or GND	5.5	—	—	± 0.5	—	± 5.0	μA
Input Leakage Current	I _{IN}	V _{IN} = V _{CC} or GND	5.5	—	—	± 0.1	—	± 1.0	
Quiescent Supply Current	I _{CC}	V _{IN} = V _{CC} or GND	5.5	—	—	8.0	—	80.0	

* : This spec indicates the capability of driving 50Ω transmission lines.
One output should be tested at a time for a 10ms maximum duration.

AC ELECTRICAL CHARACTERISTICS (C_L = 50pF, R_L = 500Ω, Input t_r = t_f = 3ns)

PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	Ta = 25°C			Ta = -40~85°C		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
Propagation Delay Time	t _{pLH}		3.3 ± 0.3	—	6.4	10.5	1.0	12.0	ns
	t _{pHL}		5.0 ± 0.5	—	4.7	7.0	1.0	8.0	
Output Enable Time	t _{pZL}		3.3 ± 0.3	—	7.1	12.3	1.0	14.0	
	t _{pZH}		5.0 ± 0.5	—	5.0	7.9	1.0	9.0	
Output Disable Time	t _{pLZ}		3.3 ± 0.3	—	5.1	8.8	1.0	10.0	
	t _{pHZ}		5.0 ± 0.5	—	4.6	6.6	1.0	7.5	
Input Capacitance	C _{IN}			—	5	10	—	10	pF
Output Capacitance	C _{OUT}			—	10	—	—	—	
Power Dissipation Capacitance	C _{PD} (1)			—	24	—	—	—	

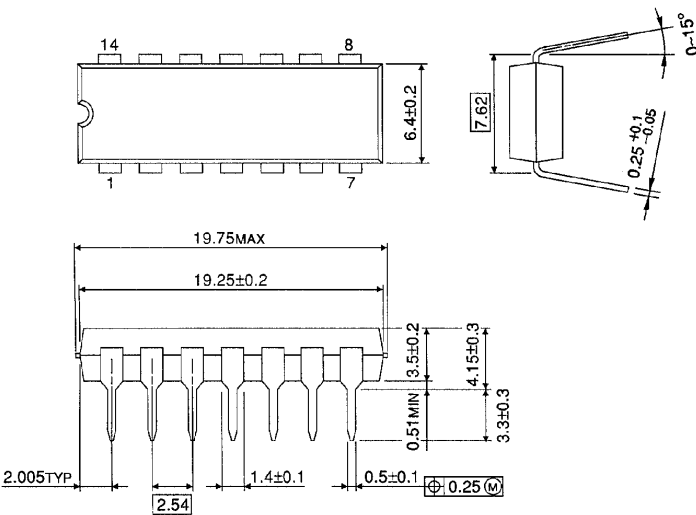
Note(1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC(opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/4 \text{ (per Gate)}$$

DIP 14PIN PACKAGE DIMENSIONS (DIP14-P-300-2.54)

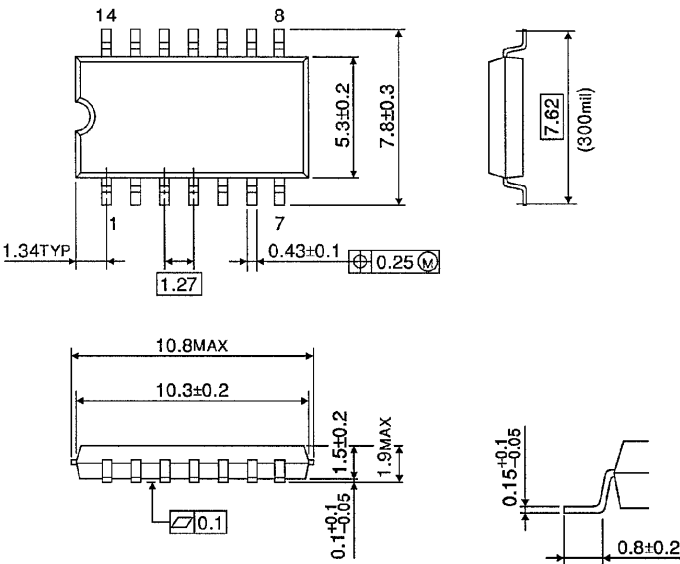
Unit in mm



Weight : 0.96g (Typ.)

SOP 14PIN (200mil BODY) PACKAGE DIMENSIONS (SOP14-P-300-1.27)

Unit in mm

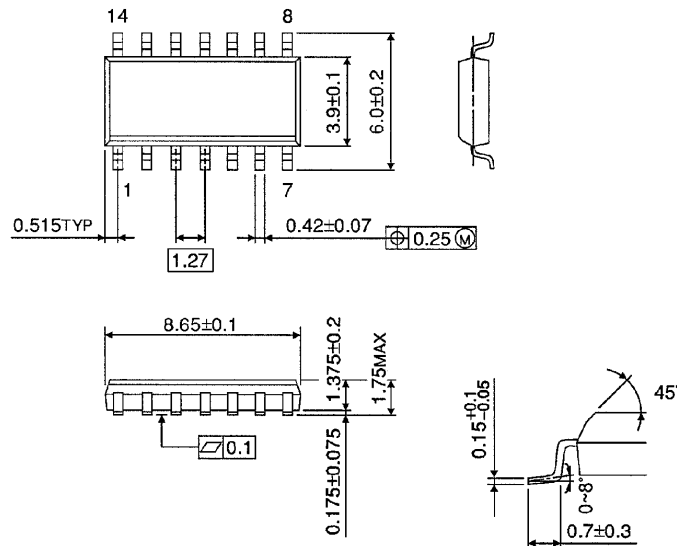


Weight : 0.18g (Typ.)

SOP 14PIN (150mil BODY) PACKAGE DIMENSIONS (SOL14-P-150 -1.27)

Unit in mm

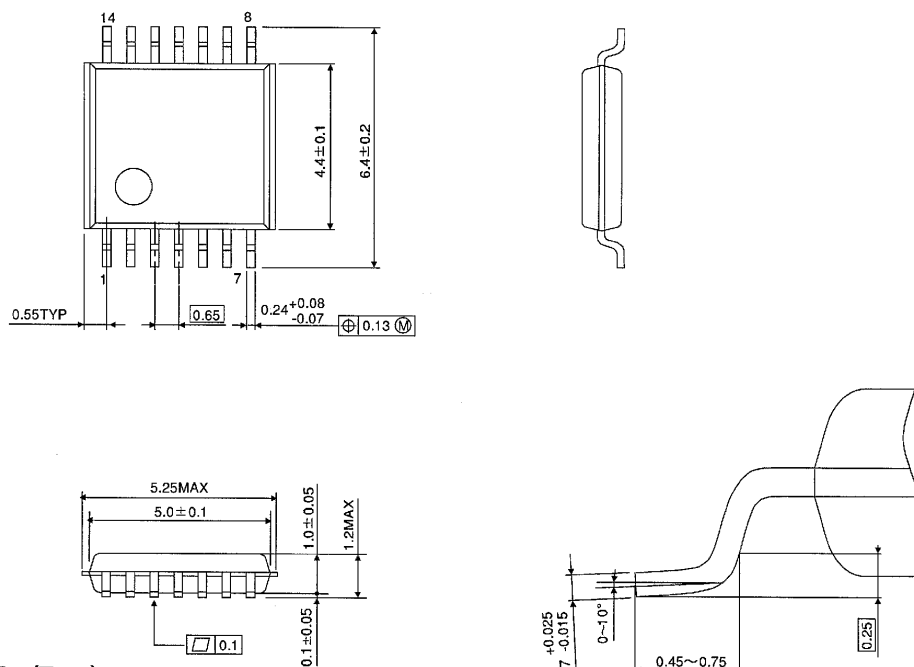
(Note) This package is not available in Japan.



Weight : 0.12g (Typ.)

TSSOP 14PIN (170mil BODY) PACKAGE DIMENSIONS (TSSOP14-P-0044-0.65)

Unit in mm



Weight : 0.06g (Typ.)

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